



ZVN4525G

Product Summary

Ĩ	V _{(BR)DSS}	Max R _{DS(on)}	Max I _D T _A = +25°C
	250V	$8.5\Omega @ V_{GS} = 10V$	310mA

Description and Applications

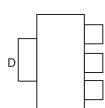
This 250V enhancement mode N-Channel MOSFET provides users with a competitive specification offering efficient power handling capability, high impedance and is free from thermal runaway and thermally induced secondary breakdown. Applications benefiting from this device include a variety of telecommunication and general high voltage circuits.

SOT223

Top View

SOT89 and SOT23-6 versions are also available.

- Earth Recall and Dialing Switches
- **Electronic Hook Switches**
- High Voltage Power MOSFET Drivers
- **Telecom Call Routers**
- Solid State Relays

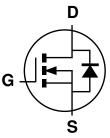


Pin Out Top-View

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250V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

Complementary P-Channel Type ZVP4525G

UL Flammability Classification Rating 94V-0 Moisture Sensitivity: Level 1 per J-STD-020

Terminals Connections: See Diagram Below

Solderable per MIL-STD-202, Method 208 @3

Weight: 0.112 grams (Approximate)

Lead-Free Finish; RoHS Compliant (Notes 1& 2)

Halogen and Antimony Free. "Green" Device (Note 3)

Case Material: Molded Plastic, "Green" Molding Compound;

Terminals: Finish - Matte Tin Annealed over Copper Leadframe;

High Voltage Low On-Resistance Fast Switching Speed Low Gate Drive Low Threshold

SOT223 Package

Mechanical Data

Case: SOT223

Equivalent Circuit

Ordering Information (Note 4)

Part Number	REEL SIZE (inches)	TAPE WIDTH (mm)	Packaging
ZVN4525GTA	7	8mm Embossed	1,000
ZVN4525GTC	13	8mm Embossed	4,000

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

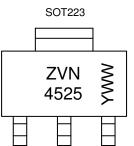
and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:



ZVN 4525 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Maximum Ratings (@T_A = +25 °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	250	V
Gate-Source Voltage		V _{GS}	±40	V
Continuous Drain Current, $V_{GS} = 10V$ (Note 5)	$\frac{T_A = +25 \degree C}{T_A = +70 \degree C}$	I _D	310 248	mA
Pulsed Drain Current (Note 7)	•	IDM	1.44	А
Continuous Source Current (Body Diode)		Is	1.1	А
Pulsed Source Current (Body Diode)		I _{SM}	1.44	А

Thermal Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25 °C (Note 5) Linear Derating Factor	PD	2 16	W mW/℃
Junction to Ambient (Note 5)	R _{0JA}	63	℃/W
Junction to Ambient (Note 6)	R _{0JA}	26	℃/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	℃

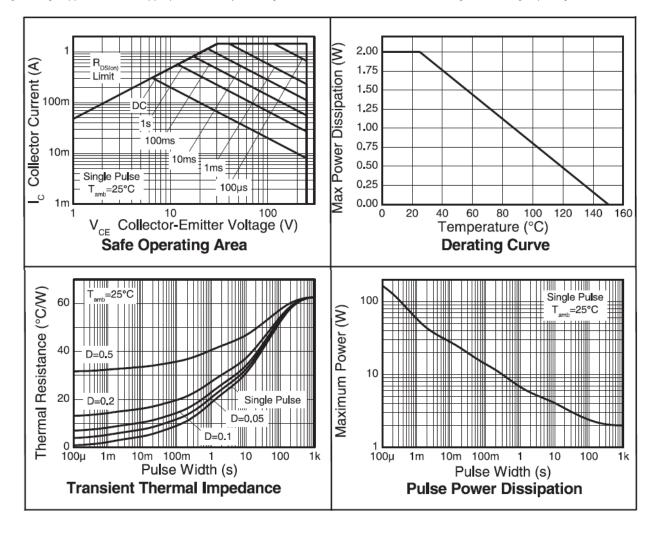
Notes: 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

6. For a device surface mounted on FR4 PCB measured at t \leq 5 seconds.

7. Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal.

NB High Voltage Applications

For high voltage applications, the appropriate industry sector guidelines should be considered with regard to voltage spacing between conductors.





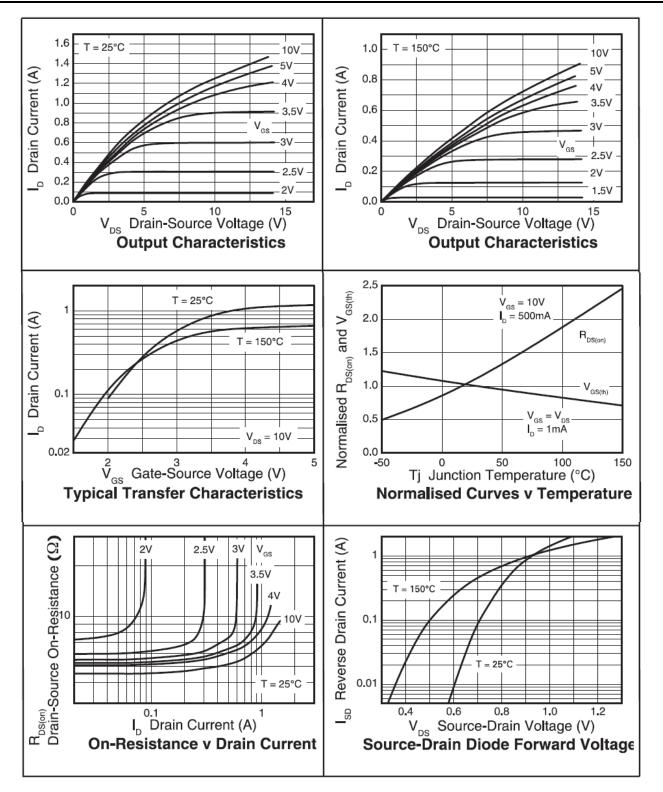
Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS			•				
Drain-Source Breakdown Voltage	BV _{DSS}	250	285		V	$I_D = 1mA$, $V_{GS} = 0V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	35	500	nA	$V_{DS} = 250V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	_	±1	±100	nA	$V_{GS} = \pm 40V, V_{DS} = 0V$	
Gate-Source Threshold Voltage	V _{GS(th)}	0.8	1.4	1.8	V	$I_D = 1mA$, $V_{DS} = V_{GS}$	
On-State Drain Current (Note 8)	I _{D(on)}	3	_	_	Α	V _{DS} = 25V, V _{GS} = 10V	
		_	5.6	8.5	Ω	$V_{GS} = 10V, I_D = 500mA$	
Static Drain-Source On-State Resistance (Note 8)	R _{DS} (ON)	_	5.9	9		$V_{GS} = 4.5V, I_D = 360mA$	
		—	6.4	9.5		$V_{GS} = 2.5V, I_D = 20mA$	
Forward Transconductance (Note 10)	g fs	0.3	0.475		S	$V_{DS} = 10V, I_D = 0.3A$	
Diode Forward Voltage (Note 8)	V_{SD}	_	—	0.97	V	$I_S = 360$ mA, $V_{GS} = 0$ V, $T_J = +25$ °C	
DYNAMIC CHARACTERISTICS (Note 10)						·	
Input Capacitance	Ciss	_	72		pF		
Output Capacitance	Coss	—	11		pF	− V _{DS} = 25 V, V _{GS} = 0V − f = 1MHz	
Reverse Transfer Capacitance	Crss	—	3.6		pF		
Total Gate Charge	Qg	—	2.6	3.65		VDS = 25V, VGS = 10V,	
Gate-Source Charge	Q _{gs}	—	0.2	0.28	nC	ID = 360mA (refer to test circuit)	
Gate-Drain Charge	Q _{gd}	_	0.5	0.70			
Turn-On Delay Time (Note 9)	t _{d(on)}	—	1.25				
Rise Time (Note 9)	tr	_	1.7	_	nc	$V_{DD} = 30V, I_D = 360mA,$	
Turn-Off Delay Time (Note 9)	t _{d(off)}	_	11.4	-	ns	$R_G = 50\Omega$, $V_{GS} = 10V$ (refer to test circuit)	
Fall Time (Note 9)	tf	_	3.5	-			
Reverse Recovery Time	t _{rr}	—	186	260	ns	IF = 360mA, di/dt = 100A/µs,	
Reverse Recovery Charge	Qrr	_	34	48	nC	TJ = +25 ℃	

8. Measured under pulsed conditions. Width=300µs. Duty cycle ≤ 2%.
9. Switching characteristics are independent of operating junction temperature.
10. For design aid only, not subject to production testing.

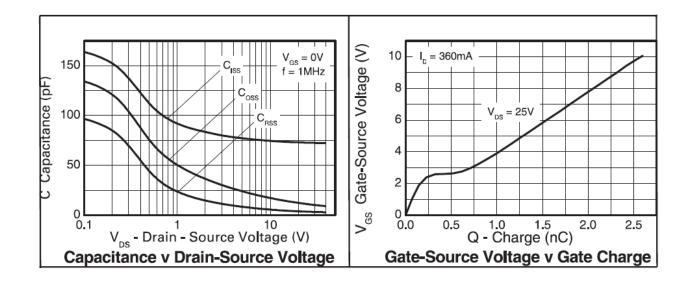


Typical Characteristics





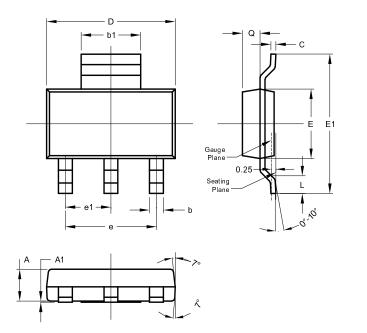
Typical Characteristics (cont.)





Package Outline Dimensions

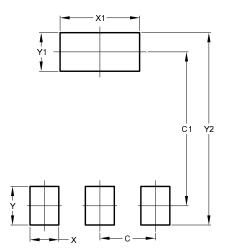
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



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SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
C2	8.00



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